



EPW

PATENT
8004-1013

IN THE U.S. PATENT AND TRADEMARK OFFICE

In re application of

Hiroaki TANAKA et al.

Conf. 4276

Application No. 10/028,778

Group 2826

Filed December 28, 2001

Examiner F. Erdem

ACTIVE MATRIX ADDRESSING LIQUID-
CRYSTAL DISPLAY DEVICESUPPLEMENTAL INFORMATION DISCLOSURE STATEMENTCommissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

In compliance with Rules 1.97 and 1.98, and in fulfillment of the duty of disclosure under Rule 1.56, the accompanying documents, copies of which are attached to this statement, are made of record on the enclosed Form PTO-1449.

A concise explanation of the relevance of these items is that these references were cited by the Korean Patent Office in an Official Action. A copy of the Korean Official Action (with Japanese translation) in which they were cited is attached hereto, with what is believed to be the pertinent portion enclosed in a wavy line. **An English translation of the enclosed portion is also attached hereto.**

Under the provisions of 37 CFR 1.97(e), the undersigned hereby certifies that each item of information contained in this Supplemental Information Disclosure Statement was first cited in any communication from a foreign Patent Of-

file in a counterpart foreign application not more than three months prior to the filing of this Statement.

Respectfully submitted,

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* Abstract provided for the Examiner's convenience

TANAKA et al.-U.S. Pat. Appl. 10/028,778
Ref. GNE-Our Ref. 8004-1013

1. Claims 1-53 of the Scope of Patent Claims of the invention of the present application relate to an active matrix addressing LCD device, characterized by the fact that it includes a transparent insulation plate, a thin film transistor, and an active matrix substrate and the like, wherein the 1st tin film of multilayer electro-conductive construction has a nitrogen concentration of 25atom% or greater. However, the invention of the present application could be invented without difficulty by one of ordinary skill in the art from the technical construction of Citation inventions 1 and 2, publications which were distributed prior to the submission of the present application, by selectively combining the technical construction of:

the Specification and Drawings of Korean Laid Open Patent Publication 2000-22736 (0/25/2000; hereafter referred to as "Citation invention 1", characterized by recording the improved adhesion characteristics of silicon nitride film by constructing of tin, the upper layer which makes contact with silicon nitride film, constructed with a between layer insulation film, and formed by the 3 layer metallic construction of TiN/Al/Ti, in which the electrode of the gate source signal line used in the referenced active matrix type LCD device includes nitrogen; and

Korean Laid Open Patent Publication 2000-62586 (10/25/2000; hereafter referred to as "Citation 2"), characterized by the fact that, in constructing the thin film transistor device of a liquid crystal display in which the gate electrode is formed by the 3 layer metallic construction of Ti/Al/TiN, the source electrode becomes the 2 layer metallic construction formed from Al and TiN, thereby enabling the prevention of Al corrosion produced when etching the gate insulation film. (Article 29 Section 2 of the Patent Law),

Addenda

Addendum 1

Korean Laid Open Patent Publication 2000-22736
(04/25/2000) 1 copy

Addendum 2

Korean Laid Open Patent Publication 2000-62586
(10/25/2000) 1 copy